

Front-end electronics dedicated to the next generation of linear collider calorimeter

# CALICE COLLABORATION

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# OUTLINE

- Requirements for ECAL
- Electronics synoptic
- Low noise preamplifier
- o Shaper
- Pipeline analog to digital converter
  - Gain 2 amplifier.
  - The comparator.
- Conclusion and schedule.

# **Requirements for ECAL**

- ECAL : Barrel with sandwich silicon-tungsten structure composed of 40 layers of reading with diodes of 1cm<sup>2</sup>.
- 34 Millions channels very low consumption
  - Pulsed power supply.
- Large dynamic range typically 14-15 bits and accuracy about 8bits.
  - Multi-gain system.
- Train = 3000 Bunch-crossing every 200ms.
  - BX = between 150ns-300ns.
    - Slow system.



# **Electronics integration**



- Reduce line capacitance  $\rightarrow$  reduce preamplifier consumption to obtain a noise less than 1/10 MIP (MIP= 40,000 e-).
- Reduce crosstalk.
- Electromagnetic shower on chip???
- Cooling issues.
- Sensor (diode) is a wafer 6cm\*6cm so 1 chip for 36 channels.
  - 34 Millions channels  $\rightarrow$  950,000 chips.
  - 34 Millions channels  $\rightarrow$  3,400 m<sup>2</sup> silicon.



# Technology choice for R&D

## The electronics for front-end will be mixed

- Need good digital performance.
- Need good analog performance.
- As cheap as possible.

## o Our choice AMS 0.35µm CMOS (c35b4)

- Perennity because used by car industry.
- Two transistors type.
  - Transistor 3.3V for digital block.
  - Transistor 5V for analog block.



# Low noise preamplifier

- $\circ~$  MIP is fixed by silicon wafer depth: 500  $\mu m$  so 40,000e-
- Noise is defined as MIP/10 so 4000e-.
  - Two types of noise :
    Serial noise :

$$e_n^2 = \frac{8 \times k \times T}{3 \times g_m} + \frac{A_f}{f}$$

The noise 1/f is neglected because we have a transistor Pmos in input.

• Parallel noise :

$$i_n^2 = 2 \times q \times Ig + \frac{4 \times k \times T}{Rf}$$

- $\circ$  Use a big transistor Pmos to have important  $g_m$ .
  - Large W 2000µm.
  - Small L 0,5µm.
  - Need current  $I_{ds}{=}200\mu A$  (power limited 1mW for preamplifier).





# Two alternatives of filtering

#### Shaper CRRC<sup>2</sup>

- $g_m = 10 \text{mA/V} \rightarrow e_n = 1.1 \text{nV}/\sqrt{\text{Hz}}$
- $I_g=30nA \rightarrow i_n=100fA/\sqrt{Hz}$



- ENC=1,430e-
- Advantage:
  - System well known
- Inconvenient:
  - Takes a large place with resistances
  - Slow reset, probably pile-up.

- Switched integrator
  - Same conditions



- <u>ENC=1,660e-</u>
- Advantage:
  - Good integration of switch
  - No pile-up
- Note:
  - Need a command signal

# Amplifier of the shaper

- Development of an amplifier in two technologies :
  - Shaper is built with an amplifier used as integrator in 0.8µm BiCMOS.
  - Gain 100 amplifier in 0.35µm CMOS to define offset.
- Mixing of two schematics
  - An amplifier with resistive common mode feedback.
  - A differential amplifier with input and output rail to rail.

# Differential amplifier with resistive common mode feedback



# Differential amplifier with rail to rail input output



LECC 2004

# **Amplifier CMOS**



# Amplifier: some tests results

#### • Two versions of amplifier

• One in 0.8µm with the amplifier in integrator. OK.



One in 0.35µm with the gain 100 amplifier :
 Offset measured=1mV, so good matching.





16 september





# ADC equivalent scheme

#### Two cases :



# Gain 2 amplifier



# **Comparator CMOS**



Comparator is used in other IN2P3 laboratories.

# Comparator tests and simulation results

| Power Supply    | ±2,5V |
|-----------------|-------|
| Consumption     | 100µA |
| Clock frequency | 5MHz  |
| Sensitivity     | 300nV |
| Offset          | 9mV   |

Simulation parasitic results

# NoiseSensitivity300μVOffset average11mV

Tests results

#### CONCLUSIONS:

- Very good modelisation.
- Must improve offset due to parasitic capacitance.
- Sensitivity in test correspond to the noise of system.

# Simulations and tests results for ADC

 First simulation results successful but in fact this simulation was done without parasitic capacitance...!!!

#### • TESTS:

- Functionality verified.
- 5 first bits are obtained.

| Power supply | ± 2,5V |  |
|--------------|--------|--|
| Dissipation  | 20mW   |  |
| Input        | ±1V    |  |
| Clock        | 5MHz   |  |

- SIMULATION with parasitic:
  - Problems of stability with amplifier.
  - Very important error on output code.



Chip send in July 2004. Area 4.17 mm<sup>2</sup>.



2.17 mm

## Improvements done for ADC

#### • Polysilicium high resistivity permits to draw big resistance

• Occupy less place on silicon.

#### • **AMPLIFIER:**

- Amplifier stabilization with higher RC on rail to rail output.
- New layout for gain 2: more compact to obtain better matching.

| С | С | С | С | С |
|---|---|---|---|---|
| С | С | С | С | С |

- COMPARATOR:
  - Offset improvement.
- More important power supply decoupling.
- Simulation results with parasitic this time
  - 10 bits obtained, wait and see for tests in October 2004.

# Conclusion

 One possible global scheme of the FE electronic exists.

- Two possibilities of filtering OK.
  - Shaper CRRC<sup>2</sup>
  - Switched integrator

• Charge preamplifier, a shaper and a comparator CMOS exist.

# Schedule

# • News improvements for ADC:

- 1.5 bit per stage for consumption.
- Not exactly the same block for 10 stages.
- To reduce consumption only one master current for all amplifiers and comparators.
- Perhaps, need digital correction. Not realized for the moment.
- Offset correction for amplifier?...